

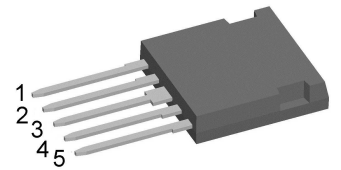
Standard Rectifier

1~ Rectifier	
V_{RRM}	= 1200 V
I_{DAV}	= 40 A
I_{FSM}	= 300 A

1~ Rectifier Bridge

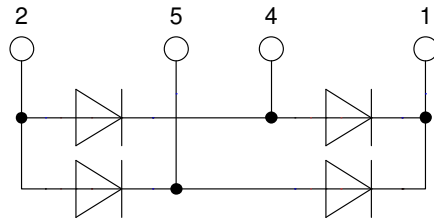
Part number

FBO40-12N



Backside: isolated

E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode Bridge for main rectification

Package: i4-Pac

- Isolation Voltage: 3000 V~
- Industry convenient outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

Terms and Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

- to perform joint risk and quality assessments;

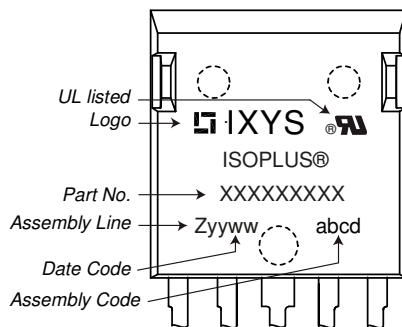
- the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					1300	V
V_{RRM}	max. repetitive reverse blocking voltage					1200	V
I_R	reverse current	$V_R = 1200$ V	$T_{VJ} = 25^\circ\text{C}$			40	μA
		$V_R = 1200$ V	$T_{VJ} = 150^\circ\text{C}$			1.5	mA
V_F	forward voltage drop	$I_F = 20$ A	$T_{VJ} = 25^\circ\text{C}$			1.17	V
		$I_F = 40$ A				1.38	V
		$I_F = 20$ A	$T_{VJ} = 150^\circ\text{C}$			1.09	V
		$I_F = 40$ A				1.37	V
I_{DAV}	bridge output current	$T_C = 130^\circ\text{C}$ rectangular	$T_{VJ} = 175^\circ\text{C}$ d = 0.5			40	A
V_{FO}	threshold voltage	} for power loss calculation only				0.79	V
r_F	slope resistance					14	m Ω
R_{thJC}	thermal resistance junction to case					1.5	K/W
R_{thCH}	thermal resistance case to heatsink				0.20		K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		100	W
I_{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^\circ\text{C}$			300	A
		t = 8,3 ms; (60 Hz), sine	$V_R = 0$ V			325	A
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150^\circ\text{C}$			255	A
		t = 8,3 ms; (60 Hz), sine	$V_R = 0$ V			275	A
I^2t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^\circ\text{C}$			450	A ² s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0$ V			440	A ² s
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150^\circ\text{C}$			325	A ² s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0$ V			315	A ² s
C_J	junction capacitance	$V_R = 400$ V; f = 1 MHz	$T_{VJ} = 25^\circ\text{C}$		4		pF

Package i4-Pac		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			35	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				9		g
F_C	mounting force with clip		20		120	N
$d_{Spp/APP}$	creepage distance on surface / striking distance through air	terminal to terminal	1.7			mm
$d_{Spb/APb}$		terminal to backside	5.1			mm
V_{ISOL}	isolation voltage	t = 1 second	3000			V
		t = 1 minute	2500			V

Product Marking

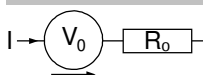


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	FBO40-12N	FBO40-12N	Tube	25	492256

Equivalent Circuits for Simulation

* on die level

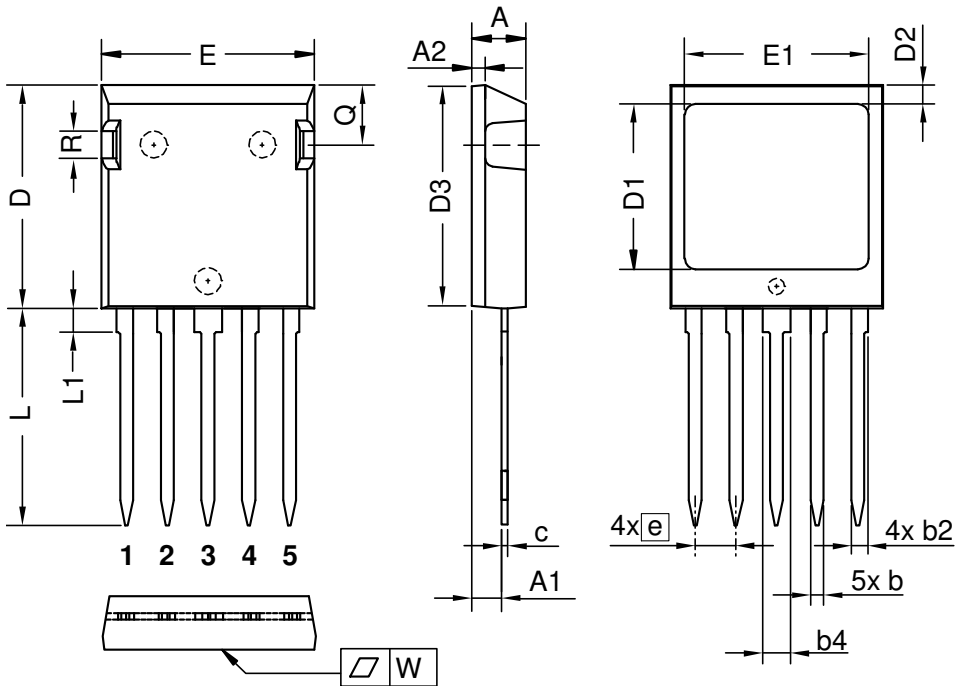
$T_{VJ} = 175\text{ °C}$



Rectifier

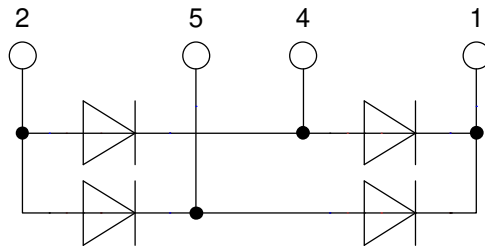
$V_{0\ max}$	threshold voltage	0.79	V
$R_{0\ max}$	slope resistance *	12	mΩ

Outlines i4-Pac



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.83	5.21	0.190	0.205
A1	2.59	3.00	0.102	0.118
A2	1.17	2.16	0.046	0.085
b	1.14	1.40	0.045	0.055
b2	1.47	1.73	0.058	0.068
b4	2.54	2.79	0.100	0.110
c	0.51	0.74	0.020	0.029
D	20.80	21.34	0.819	0.840
D1	14.99	15.75	0.590	0.620
D2	1.65	2.03	0.065	0.080
D3	20.30	20.70	0.799	0.815
E	19.56	20.29	0.770	0.799
E1	16.76	17.53	0.660	0.690
e	3.81 BSC		0.150 BSC	
L	19.81	21.34	0.780	0.840
L1	2.11	2.59	0.083	0.102
Q	5.33	6.20	0.210	0.244
R	2.54	4.57	0.100	0.180
W	-	0.10	-	0.004

Die konvexe Form des Substrates ist typ. < 0.05 mm über der Kunststoffoberfläche der Bauteilunterseite
 The convexbow of substrate is typ. < 0.05 mm over plastic surface level of device bottom side



Rectifier

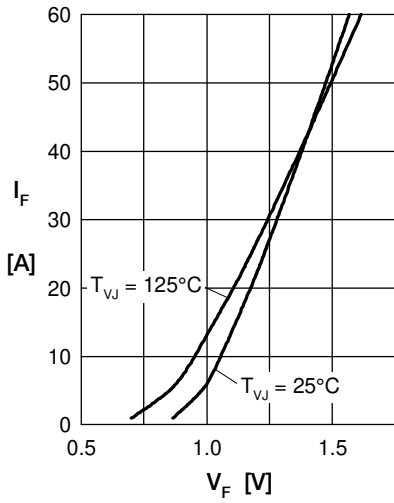


Fig. 1 Forward current versus voltage drop per diode

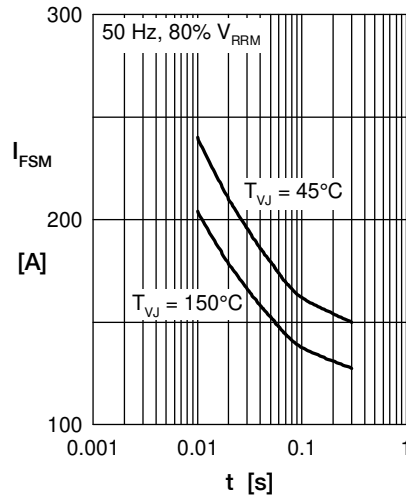


Fig. 2 Surge overload current

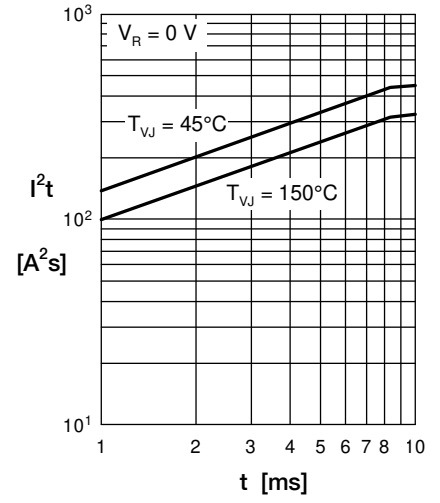


Fig. 3 I^2t versus time per diode

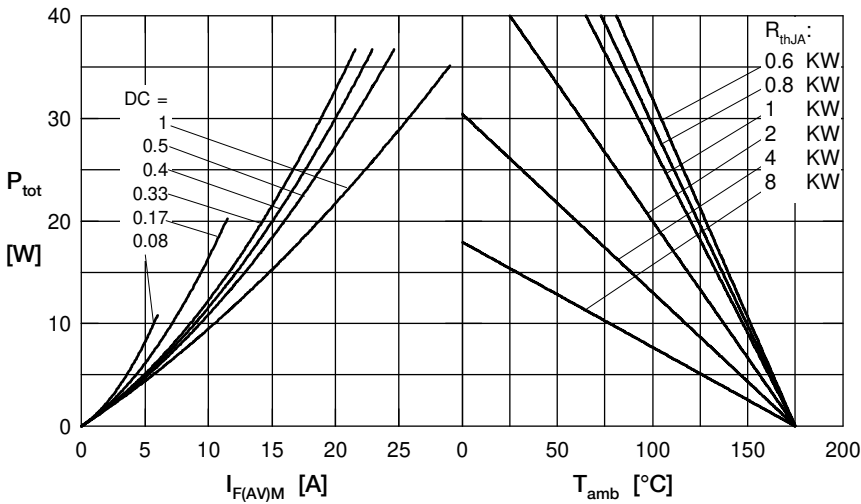


Fig. 4 Power dissipation vs. direct output current and ambient temperature

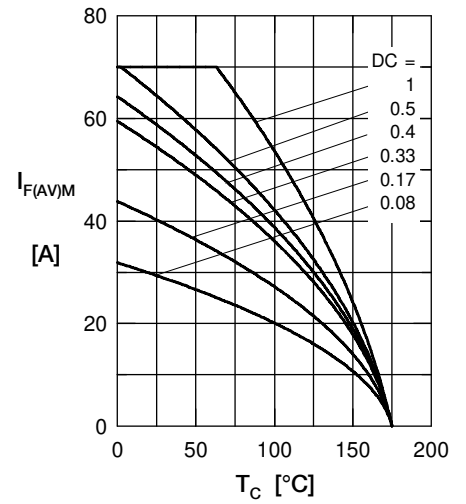


Fig. 5 Max. forward current vs. case temperature

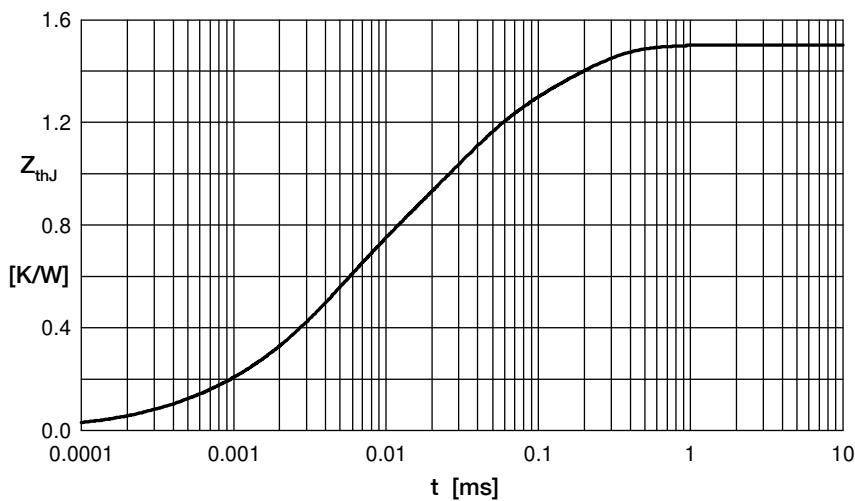


Fig. 6 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.06075	0.0004
2	0.183	0.00256
3	0.3405	0.0045
4	0.543	0.0242
5	0.3728	0.15